

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 05-206382
 (43)Date of publication of application : 13.08.1993

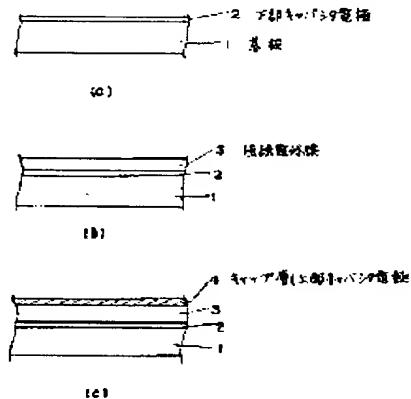
(51)Int.CI. H01L 27/04
 H01B 3/00
 H01L 41/24
 // H01L 37/02

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(54) CRYSTALLIZATION OF FERROELECTRIC FILM

(57)Abstract:

PURPOSE: To prevent the composition ratio of Pb from reducing by forming a cap layer on the surface of a ferroelectric film which contains stoichiometric Pb. CONSTITUTION: Pt is accumulated on a board 1 as a bottom capacitor electrode 2. Then, ferroelectric material which contains Pb such as PZT is accumulated and a ferroelectric film 3 is formed. At this point, the ferroelectric film has (stoichiometric) amorphous pyrochlore structure which allows most chemically stable composition. Then, Pt, etc., is accumulated on the ferroelectric film 3 and a cap layer 4 is formed. Heat treatment is performed so as to change the crystal structure of the ferroelectric film 3 to be in the perovskite condition from the pyrochlore structure. Pb in the PZT film is evaporated as PBO during the heat treatment, the reduction of the composition ratio of Pb during the heat treatment is prevented by the cap layer 4 and the stoichiometric perovskite structured fine ferroelectric film is formed.



LEGAL STATUS

[Date of request for examination] 19.01.1996
 [Date of sending the examiner's decision of rejection]
 [Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]
 [Date of final disposal for application]
 [Patent number] 2753170
 [Date of registration] 27.02.1998
 [Number of appeal against examiner's decision of rejection]
 [Date of requesting appeal against examiner's decision of rejection]
 [Date of extinction of right]